

Switching diode

1SS376

●Applications

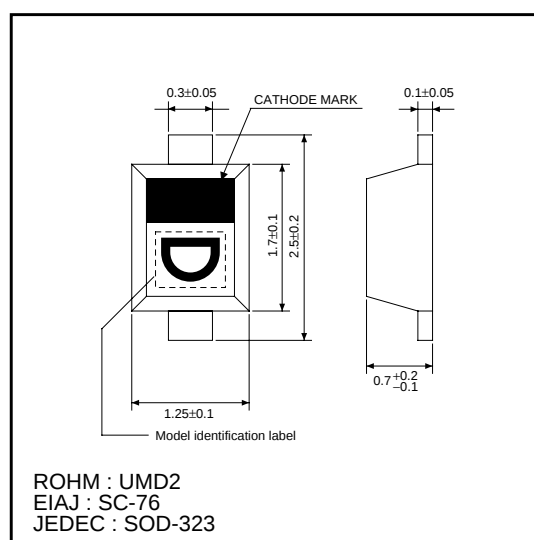
High voltage switching

●Features

- 1) Small surface mounting type. (UMD2)
- 2) $V_{RM}=300V$ guaranteed.
- 3) High reliability.

●Construction

Silicon epitaxial planar



●External dimensions (Units : mm)

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	300	V
DC reverse voltage	V_R	250	V
Peak forward current	I_{FM}	300	mA
Mean rectifying current	I_o	100	mA
Surge current (10ms)	I_{surge}	2	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+125	°C

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditons
Forward voltage	V_F	—	—	1.2	V	$I_F=100mA$
Reverse current	I_R	—	—	0.2	μA	$V_R=250V$
Reverse current	I_R	—	—	100	μA	$V_R=300V$
Capacitance between terminals	C_T	—	—	3	pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}	—	—	100	ns	$I_R=30mA, I_F=30mA, I_{rr}=3mA$

Diodes

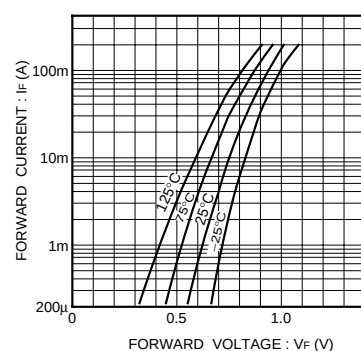
●Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.1 Forward characteristics

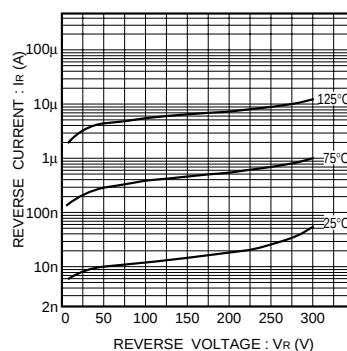


Fig.2 Reverse characteristics

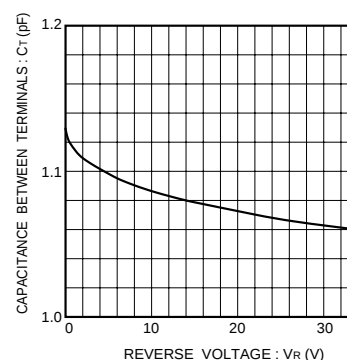


Fig.3 Capacitance between terminals characteristics

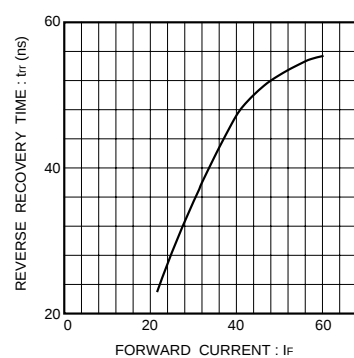


Fig.4 Reverse recovery time characteristics

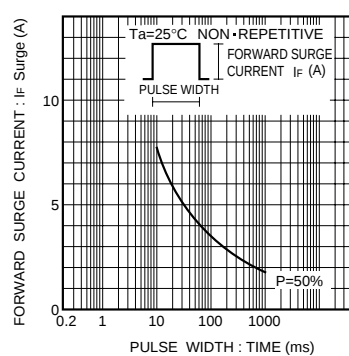
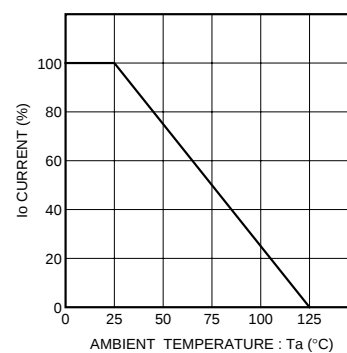


Fig.5 Surge current characteristics

Fig.6 Derating curve
(mounting on glass epoxy PCBs)